

Stress vs sputtering effects in the propagation of surface ripples produced by ion-beam sputtering

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Abstract-

Under low energy semiconductor materials, with typical sizes in the nanometric range. Recently, a theory of pattern formation has been able to account for the variability with the ion/target combination of the critical angle value separating conditions on ion incidence that induce the presence or the absence of ripples. Such a theory is based in the accumulation of stress in the damaged irradiated layer and its relaxation via surface-confined

Index Terms- Surface nanostructuring; Ion-beam sputtering; Continuum models; Stress-induced viscous flow; Ripple velocity

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